SINGLE-CHIP, LI-ION CHARGE MANAGEMENT IC FOR HANDHELD APPLICATIONS (bqTINY™)

FEATURES

- **Small 3 mm × 3 mm MLP (QFN) Package**
- **Ideal for Low-Dropout Designs for Single-Cell Li-Ion or Li-Pol Packs in Space Limited Applications**
- **Integrated Power FET and Current Sensor for Up to 1-A Charge Applications**
- **Reverse Leakage Protection Prevents Battery Drainage**
- **Integrated Current and Voltage Regulation**
- **±0.5% Voltage Regulation Accuracy**
- **Charge Termination by Minimum Current and Time**
- **Precharge Conditioning With Safety Timer**
- **Status Outputs for LED or System Interface Indicates Charge and Fault Conditions**
- **Battery Insertion and Removal Detection**
- **Works With Regulated and Unregulated Supplies**
- **Short-Circuit Protection**
- **Charge Voltage Options: 4.2 V and 4.36 V**

APPLICATIONS

- **Cellular Phones**
- **PDAs, MP3 Players**
- **Digital Cameras**
- **Internet Appliances**

DESCRIPTION

The bqTINY™ series are highly integrated Li-Ion and Li-Pol linear charge management devices targeted at space limited portable applications. The bqTINY™ series offer integrated powerFET and current sensor, reverse blocking protection, high accuracy current and voltage regulation, charge status, and charge termination, in a small package.

The bqTINY™ charges the battery in three phases: conditioning, constant current, and constant voltage. Charge is terminated based on minimum current. An internal charge timer provides a backup safety feature for charge termination. The bqTINY™ automatically re-starts the charge if the battery voltage falls below an internal threshold. The bqTINY™ automatically enters sleep mode when V_{CC} supply is removed.

In addition to the standard features, different versions of the bqTINY™ offer a multitude of additional features. These include temperature sensing input for detecting hot or cold battery packs; power good ($\overline{PG}$) output indicating the presence of valid input power; a TTL-level charge-enable input (CE) used to disable or enable the charge process; and a TTL-level timer and termination enable (TTE) input used to disable or enable the fast-charge timer and charge termination.
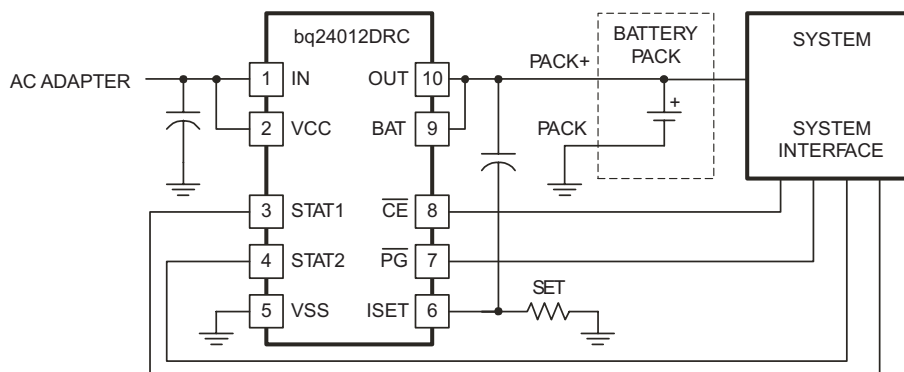
These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ORDERING INFORMATION

T_A	CHARGE REGULATION VOLTAGE (V)[1]	OPTIONAL FUNCTIONS[1]	PART NUMBER[2][3]	MARKINGS
−40°C to 125°C	4.2	$\overline{PG}$ and TS	bq24010DRCR	AZN
	4.2	$\overline{PG}$ and $\overline{CE}$	bq24012DRCR	AZP
	4.2	$\overline{CE}$ and $\overline{TTE}$	bq24013DRCR	AZQ
	4.2	$\overline{CE}$ and TS	bq24014DRCR	AZR
			bq24014DRCT	
	4.36	$\overline{CE}$ and $\overline{TTE}$	bq24018DRCR	BZH
			bq24018DRCT	

(1) Contact Texas Instruments for other options.
(2) The DRC package is available only taped and reeled. Quantities are 3,000 devices per reel (e.g. bq24010DRCR) and 250 devices per mini-reel (e.g. bq24014DRCT).
(3) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.

ABSOLUTE MAXIMUM RATINGS[1]

		VALUE	UNIT
Supply voltage range, (V_{CC} all with respect to V_{SS})		−0.3 to 18	V
Input voltage range[2]	IN, STAT1, STAT2, TS, $\overline{PG}$, $\overline{CE}$, $\overline{TTE}$	−0.3 to VCC	V
	BAT, OUT, ISET	−0.3 to 7	VDC
Voltage difference between V_{CC} and IN inputs $V_{CC} - V_{IN}$		±0.5	V
Output sink/source current	STAT1, STAT2, $\overline{PG}$	15	
Output current	IN, OUT	1.5	
T_A Operating free-air temperature range		−40 to 125	°C
T_J Junction temperature range			
T_{stg} Storage temperature		−65 to 150	°C

(1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltages are DC and with respect to VSS.

DISSIPATION RATINGS

PACKAGE	θ_{JA}	T_A < 40°C POWER RATING	DERATING FACTOR ABOVE T_A = 40°C
DRC[1]	47°C/W	1.5 W	0.021 W/°C1

(1) This data is based on using the JEDEC High-K board and the exposed die pad is connected to a copper pad on the board. This is connected to the ground plane by a 2x3 via matrix.

RECOMMENDED OPERATING CONDITIONS

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage[1][2]	3		16.5	V
V_{IN}	Input voltage[1][2]	3		16.5	V
T_J	Operating junction temperature range	−40		125	°C

(1) Pins V_{CC} and IN must be tied together.
(2) If Vin is between UVLO and 4.35V, and above the battery voltage, then the IC is active (can deliver some charge to the battery), but the IC will have limited or degraded performance (some functions may not meet data sheet specifications). The battery may be undercharged ($V_{O(reg)}$ less than in the specification), but will not be overcharged ($V_{O(reg)}$ will not exceed specification).

Product Folder Link(s): *bq24010, bq24012 bq24013, bq24014, bq24018*

ELECTRICAL CHARACTERISTICS

over 0°C ≤ T_J ≤ 125°C and recommended supply voltage, (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
INPUT CURRENT							
$I_{CC(VCC)}$	VCC current	$V_{CC} > V_{CC(min)}$, STATx pins in OFF state		0	3.5	5	mA
$I_{CC(SLP)}$	Sleep current	Sum of currents into OUT and BAT pins, $V_{CC} < V_{(SLP)}$				5	µA
$I_{IB(BAT)}$	Input bias current on BAT pin					500	nA
$I_{IB(TS)}$	Input current on TS pin	$V_{I(TS)}$ ≤ 10 V				1	
$I_{IB(CE)}$	Input current on $\overline{CE}$ pin					1	µA
$I_{IB(\overline{TTE})}$	Input bias current on $\overline{TTE}$ pin					1	
VOLTAGE REGULATION $V_{O(REG)} + V_{(DO-MAX)}$ ≤ V_{CC}, $I_{(TERM)} < I_{O(OUT)}$ ≤ 1 A							
$V_{O(REG)}$	Output voltage, $V_{O(REG)}$	bq24010, bq24012, bq24013, bq24014			4.2		V
		bq24018			4.36		
	Voltage regulation accuracy	T_A = 25°C		−0.5%		0.5%	
				−1%		1%	
$V_{(DO)}$	Dropout voltage ($V_{(IN)} − V_{(OUT)}$)	$V_{O(REG)} + V_{(DO-MAX)}$) ≤ V_{CC}, $I_{O(OUT)}$ = 1A			650	790	mV
CURRENT REGULATION							
$I_{O(OUT)}$[(1)]	Output current range	V_{CC} ≥ 4.5 V, V_{IN} ≥ 4.5 V, $V_{I(BAT)} > V_{(LOWV)}$, $V_{IN} − V_{I(BAT)} > V_{(DO-MAX)}$		100		1000	mA
		See note [(2)]		25		100	
$V_{(SET)}$	Output current set voltage	Voltage on ISET pin, V_{CC} ≥ 4.5 V, V_{IN} ≥ 4.5 V, $V_{I(BAT)} > V_{(LOWV)}$, $V_{IN} − V_{I(BAT)} > V_{(DO-MAX)}$, $V_{O(REG)}$ = 4.2 V	bq24010, bq24012, bq24013, bq24014	2.45	2.50	2.55	V
			bq24018	2.548	2.6	2.652	V
$K_{(SET)}$	Output current ISET factor	50 mA ≤ $I_{O(OUT)}$ ≤ 1000 mA, $V_{(LOWV)} < V_{(OUT)} < V_{(RCH)}$		315	335	355	
		25 mA ≤ $I_{O(OUT)}$ < 50 mA, $V_{(LOWV)} < V_{(OUT)} < V_{(RCH)}$		315	372	430	
		10 mA ≤ $I_{O(OUT)}$ < 100 mA, $V_{(OUT)} < V_{(LOWV)}$		350		1000	
		2.5 mA ≤ $I_{O(OUT)}$ < 10 mA, $V_{(OUT)} < V_{(LOWV)}$			450		
		2.5 mA ≤ $I_{O(OUT)} < I_{(PGM)}$, $V_{(OUT)} < V_{(RCH)}$			355[(3)]		
PRECHARGE AND SHORT-CIRCUIT CURRENT REGULATION							
$V_{(LOWV)}$	Precharge to fast-charge transition threshold	Voltage on BAT pin		2.80	2.95	3.10	V
$V_{(SC)}$	Precharge to short-charge transition threshold	Voltage on BAT pin		1	1.4	1.8	V
$I_{O(PRECHG)}$[(4)]	Precharge range	$V_{(SC)} < V_{I(BAT)} < V_{(LOWV)}$, t < $t_{(PRECHG)}$		10		100	mV
$V_{(PRECHG)}$	Precharge set voltage	Voltage on ISET pin, $V_{(SC)} < V_{I(BAT)} < V_{(LOWV)}$		225	250	280	mV
I_{SC}	Short circuit current	$V_{(SC)} > V_{I(BAT)}$		660	900	1200	µA

$$I_{O(OUT)} = \frac{\left(K_{(SET)} \times V_{(SET)}\right)}{R_{(SET)}}$$

(1)

(2) Specified by design. Not production tested.

(3) The ISET pin may be used as a current monitor during voltage regulation by applying the following equation:

$$I_{O(OUT)} = K_{(ISET)} \times \left(\frac{V_{(ISET)}}{R_{(ISET)} + 10\mu A}\right)$$

This equation is also used for calculating the termination point.

$$I_{O(PRECHG)} = \frac{\left(K_{(SET)} \times V_{(PRECHG)}\right)}{R_{(SET)}}$$

(4)

ELECTRICAL CHARACTERISTICS (Continued)

over 0°C ≤ T_J ≤ 125°C and recommended supply voltage, (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
CHARGE TAPER AND TERMINATION DETECTION						
$I_{(TAPER)}$[1]	Charge taper detection range	$V_{I(BAT)} > V_{(RCH)}$, $t < t_{(TAPER)}$	10		100	mA
$V_{(TAPER)}$	Charge taper detection set voltage	Voltage on ISET pin, $V_{I(BAT)} > V_{(RCH)}$, $t < t_{(TAPER)}$, $V_{I(BAT)} = V_{O(REG)}$	225	250	275	mV
$V_{(TERM)}$	Charge termination detection set voltage	Voltage on ISET pin, $V_{I(BAT)} = V_{O(REG)}$, $V_{I(BAT)} > V_{(RCH)}$, $I_{(TERM)} = K_{(SET)}$ ɔ $V_{(TERM)}$ /$R_{(SET)}$	5	17.5	50	mV
TEMPERATURE COMPARATOR						
$V_{(TS1)}$	Lower threshold	Voltage on TS pin	29	30	31	
$V_{(TS2)}$	Upper threshold	Voltage on TS pin	60	61	62	%VCC
	Hysteresis			1		
BATTERY RECHARGE THRESHOLD						
$V_{(RCH)}$	Recharge threshold		$V_{O(REG)}$ −0.135	$V_{O(REG)}$ −0.1	$V_{O(REG)}$ −0.075	V
STAT1, STAT2, AND $\overline{PG}$ OUTPUTS						
V_{OL}	Output (low) saturation voltage	I_O = 10 mA			0.5	V
CHARGE ENABLE ($\overline{CE}$) AND TIMER AND TERMINATION ENABLE ($\overline{TTE}$) INPUTS						
V_{IL}	Low-level input voltage	I_{IL} = 1 µA	0		0.8	V
V_{IH}	High-level input voltage	I_{IL} = 1 µA	2.0			
TIMERS						
$t_{(PRECHG)}$	Precharge time		1, 548	2,065	2,581	
$t_{(TAPER)}$	Taper time		1, 548	2,065	2,581	s
$t_{(CHG)}$	Charge time		15, 480	20,650	25,810	
SLEEP COMPARATOR						
V_{SLP}	Sleep mode entry threshold voltage	V_{POR} ≤ $V_{(IBAT)}$ ≤ $V_{O(REG)}$			V_{CC} ≤ $V_{I(BAT)}$ + 30 mV	V
	Sleep mode exit threshold voltage	V_{POR} ≤ $V_{(IBAT)}$ ≤ $V_{O(REG)}$	V_{CC} ≥ $V_{I(BAT)}$ + 22 mV			
	Sleep mode deglitch time	VCC decreasing below threshold, 100 ns fall time, 10 mV overdrive	250		650	ms
BATTERY DETECTION THRESHOLDS						
$I_{(DETECT)}$	Battery detection current	2 V ≤ $V_{(IBAT)}$ ≤ $V_{(RCH)}$	−3.1	−4.6	−6.1	mA
$I_{(DETECT)}$	battery detection time	2 V ≤ $V_{(IBAT)}$ ≤ $V_{(RCH)}$	100	125	150	ms
$I_{(FAULT)}$	Fault current	$V_{(IBAT)} < V_{(RCH)}$ and/or $t > t_{(PRECHG)}$	660	900	1200	µA
POWER-ON RESET AND INPUT VOLTAGE RAMP RATE						
V_{POR}[2]	Power-on reset threshold voltage		225	2.5	2.75	V

$$I_{O(TAPER)} = \frac{\left(K_{(SET)} \times V_{(TAPER)}\right)}{R_{(SET)}}$$

(1)
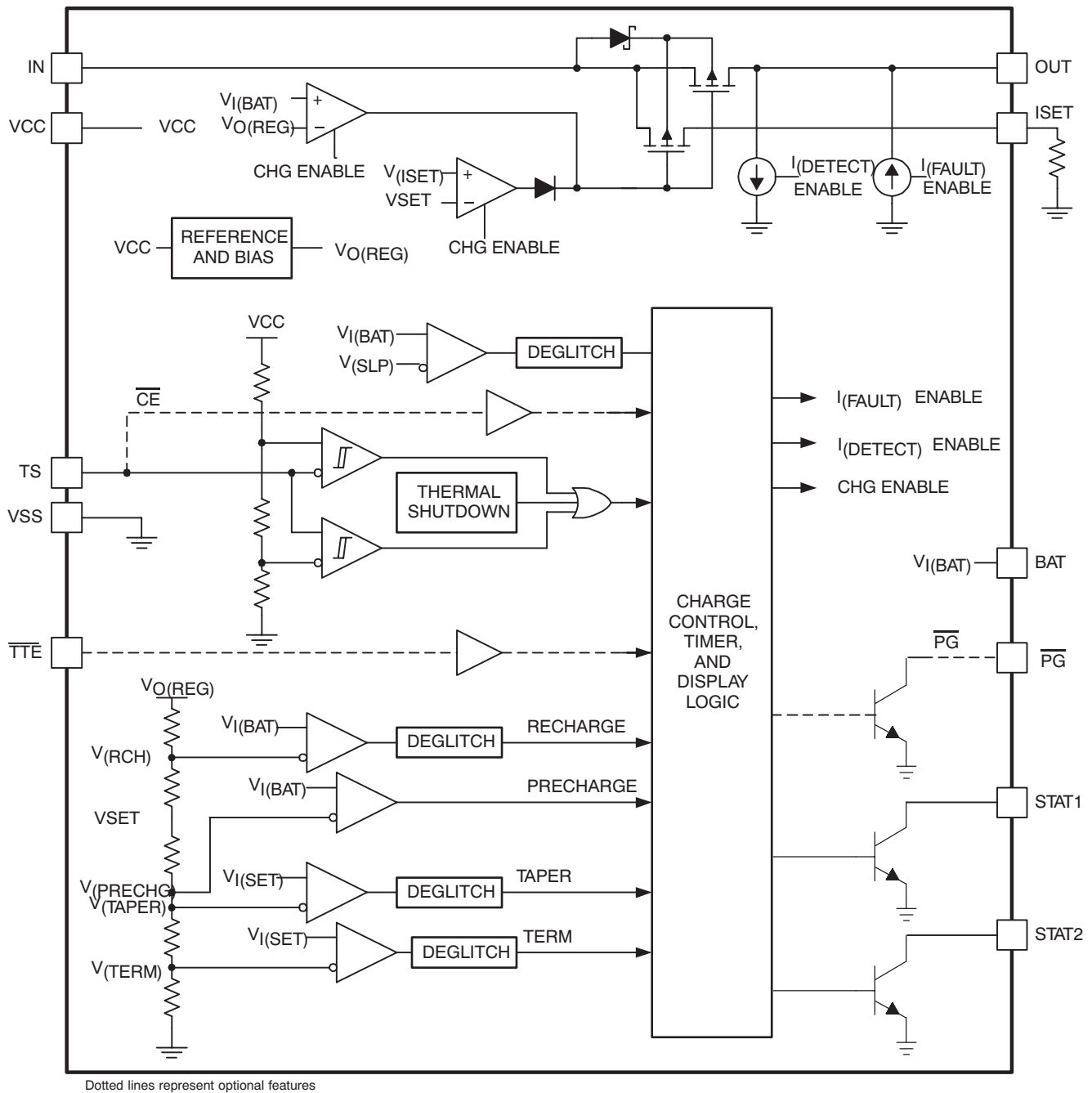(2) Specified by design. Not production tested.

DEVICE INFORMATION

DRC PACKAGE
(TOP VIEW)

VSS STAT2 STAT1 VCC IN

| 5 | 4 | 3 | 2 | 1 |

bq24010DRC

| 6 | 7 | 8 | 9 | 10 |

ISET PG TS BAT OUT

DRC PACKAGE
(TOP VIEW)

VSS STAT2 STAT1 VCC IN

| 5 | 4 | 3 | 2 | 1 |

bq24012DRC

| 6 | 7 | 8 | 9 | 10 |

ISET PG CE BAT OUT

DRC PACKAGE
(TOP VIEW)

VSS STAT2 STAT1 VCC IN

| 5 | 4 | 3 | 2 | 1 |

bq24013DRC
and
bq24018DRC

| 6 | 7 | 8 | 9 | 10 |

ISET CE TTE BAT OUT

DRC PACKAGE
(TOP VIEW)

VSS STAT2 STAT1 VCC IN

| 5 | 4 | 3 | 2 | 1 |

bq24014DRC

| 6 | 7 | 8 | 9 | 10 |

ISET CE TS BAT OUT
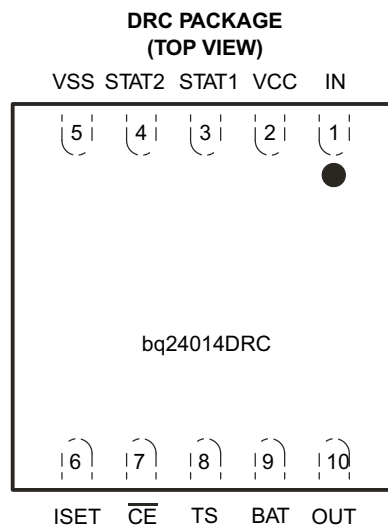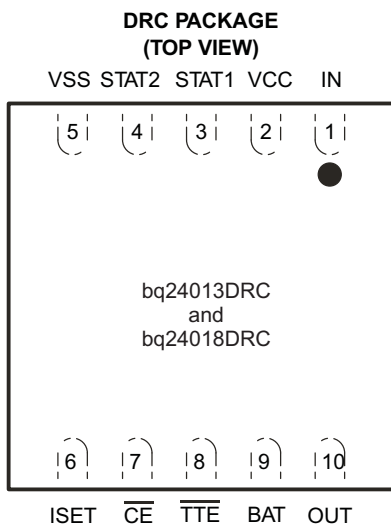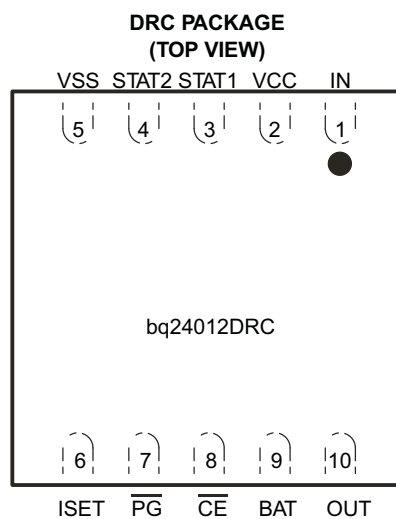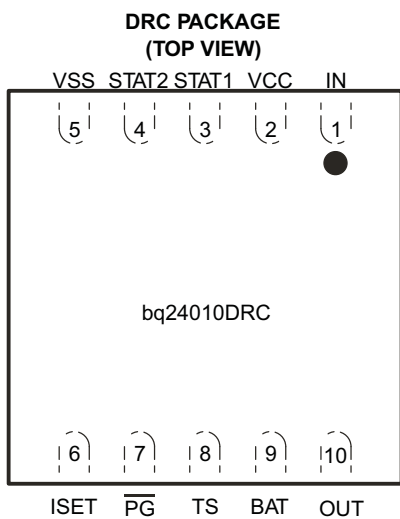
TERMINAL FUNCTIONS

TERMINAL					I/O	DESCRIPTION
NAME	bq24010	bq24012	bq24013 and bq24018[1]	bq24014		
BAT	9	9	9	9	I	Battery voltage sense input
$\overline{CE}$	–	8	7	7	I	Charge enable input (active low)
IN	1	1	1	1	I	Charge input voltage. This input must be tied to the VCC pin.
ISET	6	6	6	6	O	Charge current set point
OUT	10	10	10	10	O	Charge current output
$\overline{PG}$	7	7	–	–	O	Power good status output (open collector)
STAT1	3	3	3	3	O	Charge status output 1 (open collector)
STAT2	4	4	4	4	O	Charge status output 2 (open collector)
$\overline{TTE}$	–	–	8	–	I	Timer and termination enable input (active low)
TS	8	–	–	8	I	Temperature sense input
VCC	2	2	2	2	I	VCC supply input
VSS	5	5	5	5	–	Ground input
Exposed Thermal PAD	Pad	Pad	Pad	Pad	–	There is an internal electrical connection between the exposed thermal pad and V_{SS} pin of the device. The exposed thermal pad must be connected to the same potential as the Vss pin on the printed circuit board. Do not use the thermal pad as the primary ground input for the device. VSS pin must be connected to ground at all times.

(1) The bq24018 is in product preview status.

FUNCTIONAL BLOCK DIAGRAM

Dotted lines represent optional features

TYPICAL CHARACTERISTICS

DROPOUT VOLTAGE
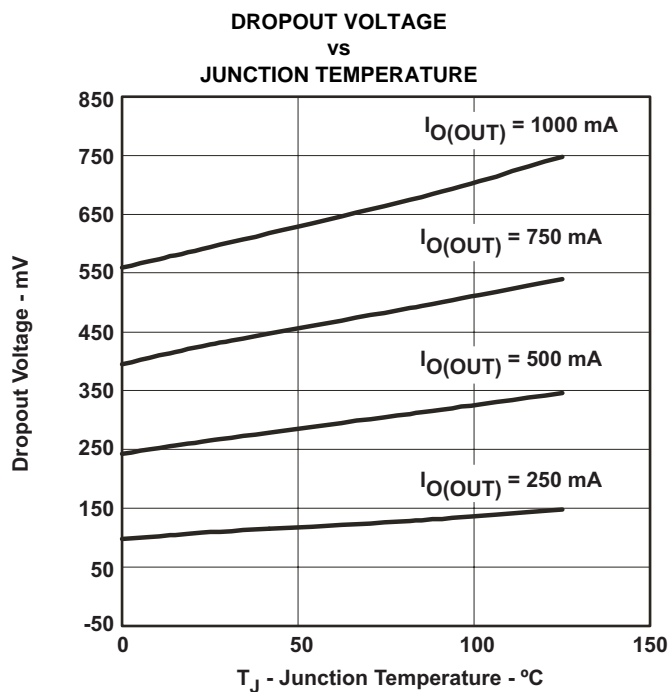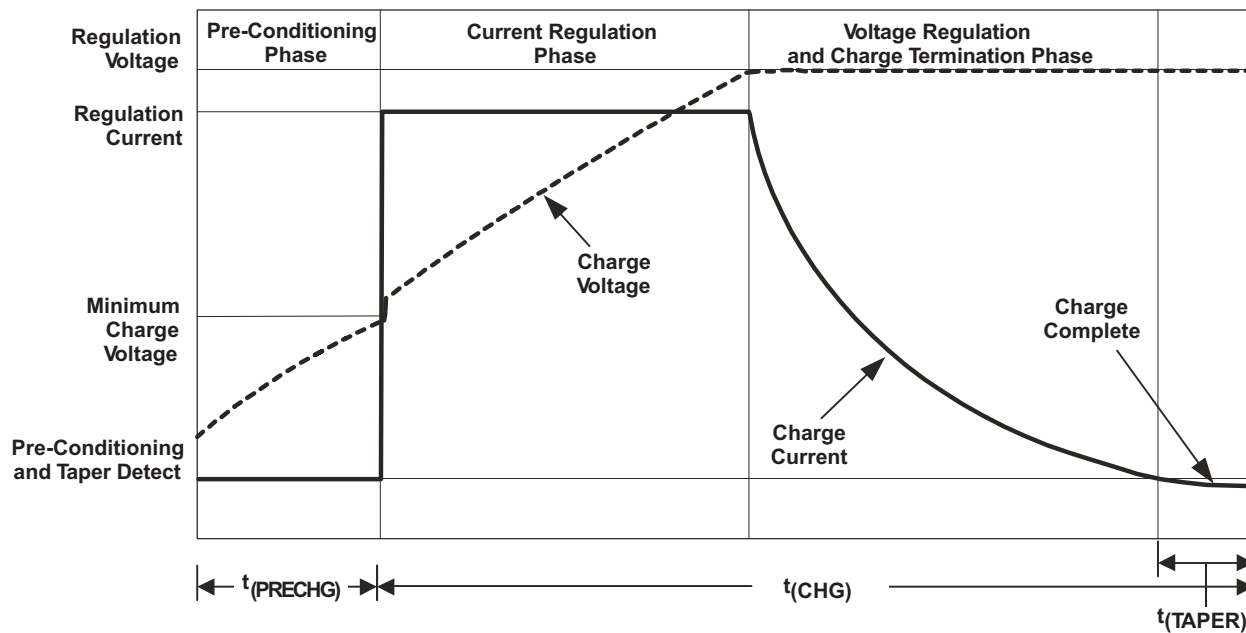**vs**
JUNCTION TEMPERATURE

Figure 1.

Figure 2. Typical Charging Profile

FUNCTIONAL DESCRIPTION

The bqTINY™ supports a precision Li-Ion, Li-Pol charging system suitable for single-cells. Figure 2 shows a typical charge profile, application circuit and Figure 5 shows an operational flow chart.
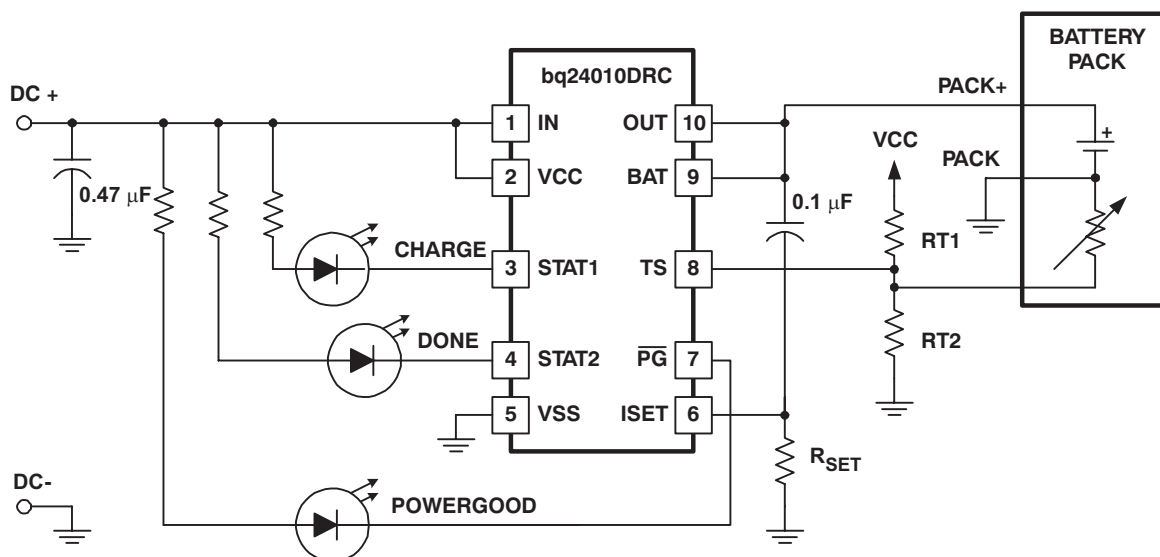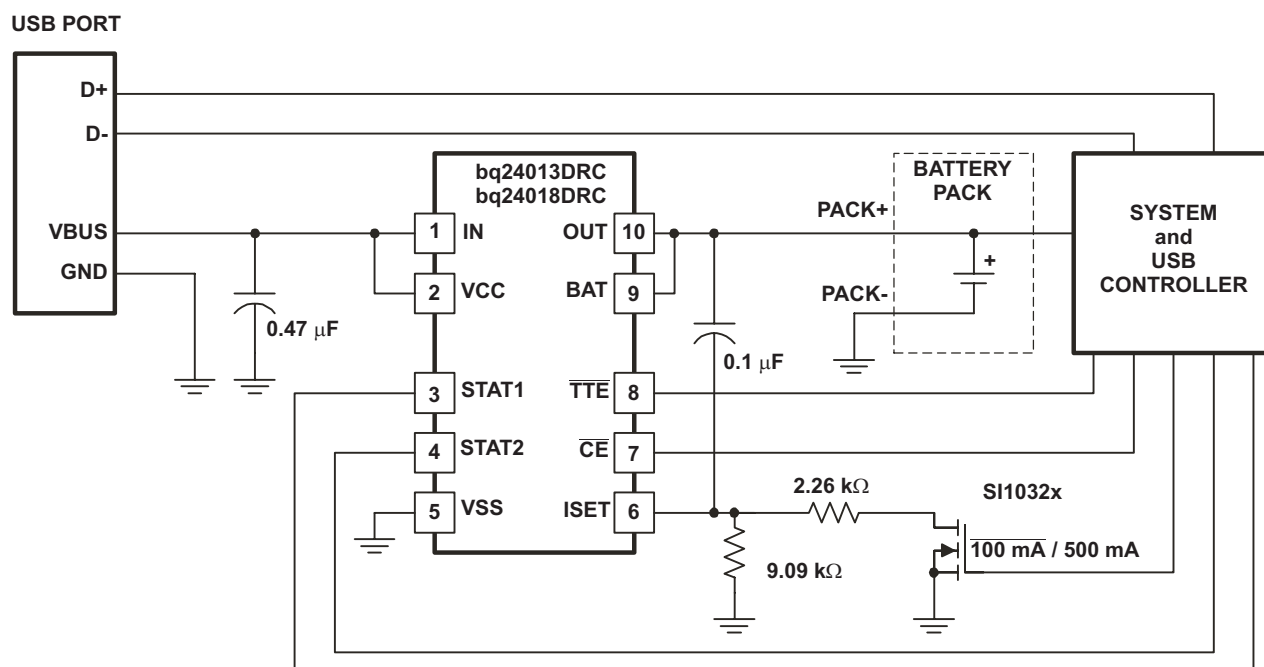

Figure 3. Typical Application Circuit
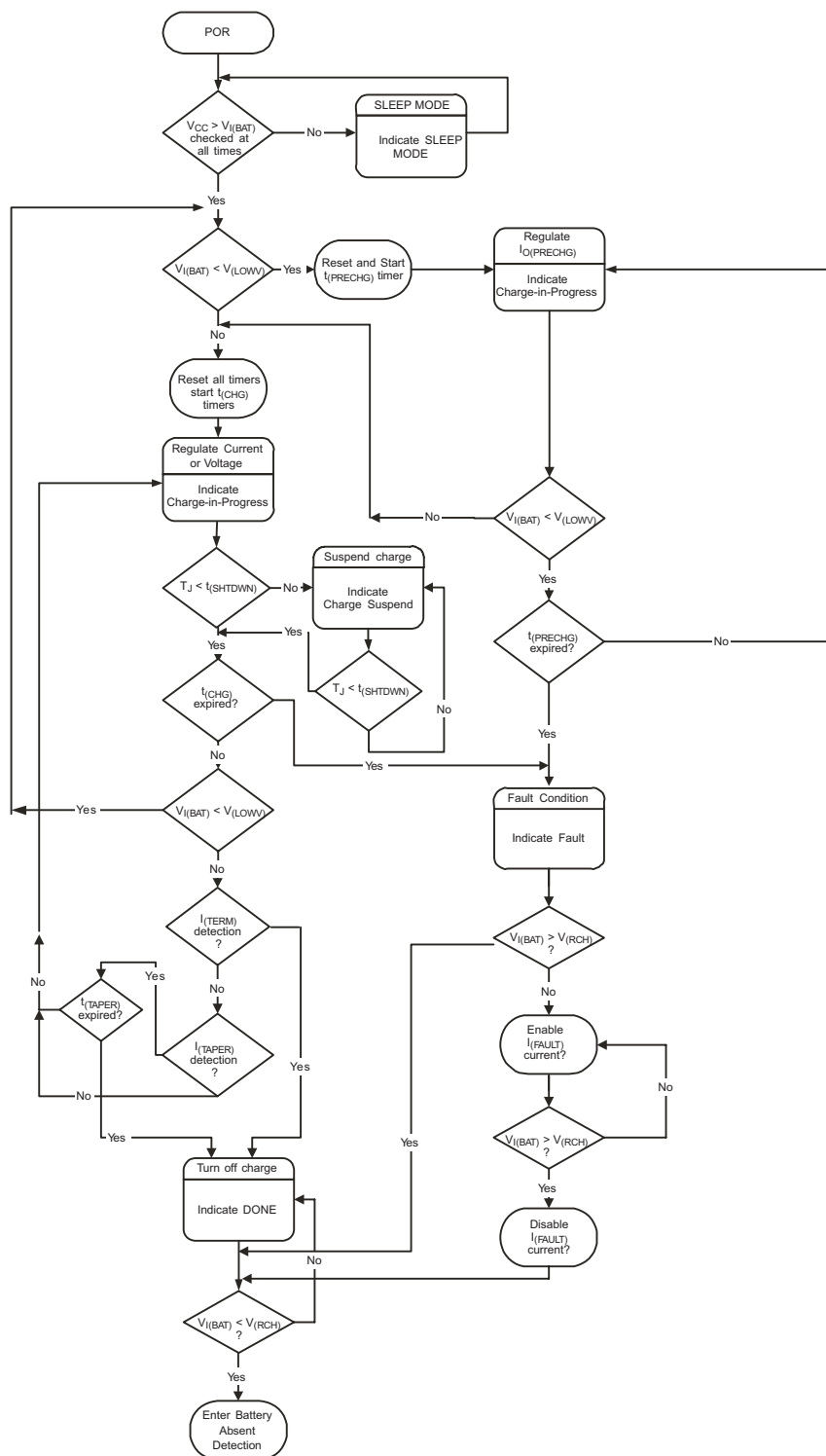

Figure 4. USB Charger Circuit

bq24010, bq24012
bq24013, bq24014, bq24018

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TEXAS
INSTRUMENTS

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Figure 5. Operational Flow Chart

TEMPERATURE QUALIFICATION

NOTE:

The temperature qualifications apply only to versions with temperature sense input (TS) pin option (bq24020 and bq24014).

Versions of the bqTINY with the TS pin option, continuously monitor battery temperature by measuring the voltage between the TS and VSS pins. A negative temperature coefficient thermistor (NTC) and an external voltage divider typically develops this voltage (see Figure 3). The bqTINY compare this voltage against the internal $V_{(TS1)}$ and $V_{(TS2)}$ thresholds to determine if charging is allowed (see Figure 6). The temperature sensing circuit is immune to any fluctuation in V_{CC} since both the external voltage divider and the internal thresholds are ratiometric to V_{CC}.

Once a temperature outside the $V_{(TS1)}$ and $V_{(TS2)}$ thresholds is detected the bqTINY immediately suspend the charge. The bqTINY suspends charge by turning off the power FET and holding the timer value (i.e. timers are NOT reset). Charge is resumed when the temperature returns to the normal range.
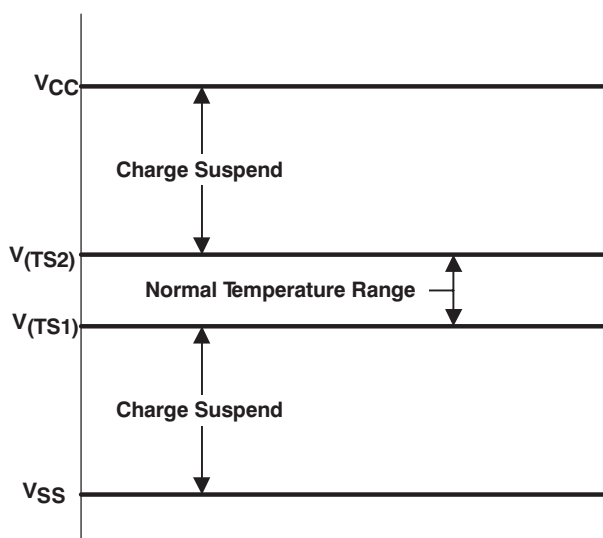

Figure 6. TS Pin Thresholds

The resistor values of R_{T1} and R_{T2} are calculated by Equation 1 and Equation 2 (for NTC Thermistors).

$$R_{T1} = \frac{(5 \times R_{TH} \times R_{TC})}{(3 \times (R_{TC} - R_{TH}))} \tag{1}$$

$$R_{T2} = \frac{(5 \times R_{TH} \times R_{TC})}{(2 \times R_{TC}) - (7 \times R_{TH})} \tag{2}$$

Where R_{TC} is the cold temperature resistance and R_{TH} is the hot temperature resistance of thermistor, as specified by the thermistor manufacturer.

R_{T1} or R_{T2} can be omitted If only one temperature (hot or cold) setting is required. Applying a constant voltage between the V_{TS1} and V_{TS2} thresholds to pin TS disables the temperature-sensing feature.

BATTERY PRE-CONDITIONING

During a charge cycle if the battery voltage is below the $V_{(LOWV)}$ threshold, the bqTINY applies a precharge current, $I_{O(PRECHG)}$, to the battery. This feature revives deeply discharged cells. The resistor connected between the ISET and V_{SS}, R_{SET}, determines the precharge rate. The $V_{(PRECHG)}$ and $K_{(SET)}$ parameters are specified in the specifications table.

$$I_{O(PRECHG)} = \frac{\left(V_{(PRECHG)} \times K_{(SET)}\right)}{R_{(SET)}}$$

(3)

The bqTINY activates a safety timer, $t_{(PRECHG)}$, during the conditioning phase. If $V_{(LOWV)}$ threshold is not reached within the timer period, the bqTINY turns off the charger and enunciates FAULT on the STAT1 and STAT2 pins. Refer to *Timer Fault Recovery* section for additional details.

BATTERY CHARGE CURRENT

The bqTINY offers on-chip current regulation with programmable set point. The resistor connected between the ISET and V_{SS}, R_{SET}, determines the charge rate. The $V_{(SET)}$ and $K_{(SET)}$ parameters are specified in the specifications table.

$$I_{O(OUT)} = \frac{\left(K_{(SET)} \times V_{(SET)}\right)}{R_{(SET)}}$$

(4)

BATTERY VOLTAGE REGULATION

Voltage regulation feedback is accomplished through the BAT pin. This input is tied directly and close to the positive side of the battery pack. The bqTINY monitors the battery-pack voltage between the BAT and VSS pins. When the battery voltage rises to $V_{O(REG)}$ threshold, the voltage regulation phase begins and the charging current begins to taper down.

As a safety backup, the bqTINY also monitors the charge time in the charge mode. If termination does not occur within this time period, $t_{(CHG)}$, the bqTINY turns off the charger and enunciates FAULT on the STAT1 and STAT1 pins. Refer to the *Timer Fault Recovery* section for additional details.

CHARGE TAPER DETECTION, TERMINATION AND RECHARGE

The bqTINY monitors the charging current during the voltage regulation phase. Once the taper threshold, $I_{(TAPER)}$, is detected the bqTINY initiates the taper timer, $t_{(TAPER)}$. Charge is terminated after the timer expires. The resistor connected between the ISET and V_{SS}, R_{SET}, determines the taper detection level. The $V_{(TAPER)}$ and $K_{(SET)}$ parameters are specified in the specifications table.

$$I_{(TAPER)} = \frac{\left(V_{(TAPER)} \times K_{(SET)}\right)}{R_{(SET)}}$$

(5)

The bqTINY resets the taper timer in the event that the charge current returns above the taper threshold, $I_{(TAPER)}$.

In addition to the taper current detection, the bqTINY terminates charge in the event that the charge current falls below the $I_{(TERM)}$ threshold. This feature allows for quick recognition of a battery removal condition or insertion of a fully charged battery. Note that taper timer is not used for $I_{(TERM)}$ detection. The resistor connected between the ISET and V_{SS}, R_{SET}, determines the taper detection level. The $V_{(TERM)}$ and $K_{(SET)}$ parameters are specified in the specifications table.

$$I_{(TERM)} = \frac{\left(V_{(TERM)} \times K_{(SET)}\right)}{R_{(SET)}}$$

(6)

After charge termination, the bqTINY restarts the charge once the voltage on the BAT pin falls below the V(RCH) threshold. This feature keeps the battery at full capacity at all times. See the *Battery Absent Detection section* for additional details.

SLEEP MODE

The bqTINY enters the low-power sleep mode if the V_{CC} is removed from the circuit ($\overline{PG}$ pin is high impedance). This feature prevents draining the battery during the absence of V_{CC}. The status pins do not function when in sleep mode or when $V_{CC} < V_{POR}$ and default to the OFF state.

CHARGE STATUS OUTPUTS

The open-collector STAT1 and STAT2 outputs indicate various charger operations as shown in the following table. These status pins can be used to drive LEDs or communicate to the host processor. Note that OFF indicates the open-collector transistor is turned off. When $V_{CC} < V_{POR}$ or $V_{CC} < V_{BAT}$ (Sleep Mode – PG OFF) the STAT pins default to their OFF state. Note that this STAT1/STAT2 OFF/OFF state is shared by several operating conditions. Monitoring IN, BAT, $\overline{PG}$ and TS, it is possible to decode the actual fault condition.

Table 1. Status Pins Summary

CHARGE STATE	STAT1	STAT2
Charge-in-progress	ON	OFF
Charge done	OFF[(1)]	ON
Battery absent Charge suspend (temperature) Timer fault Sleep mode	OFF	OFF

(1) OFF means the open-collector output transistor on the STAT1 or STAT2 pins is in an off state.

$\overline{PG}$ OUTPUT

The open-collector $\overline{PG}$ (power good) indicates when the ac adapter (i.e., V_{CC}) is present. The $\overline{PG}$ bipolar transistor turns ON when a valid V_{CC} is detected. This output is turned off in the sleep mode. The PG pin can be used to drive an LED or communicate to the host processor.

$\overline{CE}$ INPUT (CHARGE ENABLE)

The $\overline{CE}$ digital input is used to disable or enable the charge process. A low-level signal on this pin enables the charge and a high-level signal disables the charge. A high-to-low transition on this pin also resets all timers and fault conditions and starts a new charge cycle.

$\overline{TTE}$ INPUT (TIMER AND TERMINATION ENABLE)

The $\overline{TTE}$ digital input is used to disable or enable the fast-charge timer and charge termination. A low-level signal on this pin enables the fast-charge timer and termination and a high-level signal disables this feature. A high-to-low transition on this pin also resets all timers.

THERMAL SHUTDOWN AND PROTECTION

The bqTINY monitors the junction temperature, T_J, of the die and suspends charging if T_J exceeds 155°C. Charging resumes when T_J falls below approximately 130°C.

BATTERY ABSENT DETECTION

For applications with removable battery packs, bqTINY provides a battery absent detection scheme to reliably detect insertion and/or removal of battery packs.

The voltage at the BAT pin is held above the battery recharge threshold, $V_{(RCH)}$, by the charged battery following fast charging. When the voltage at the BAT pin falls to the recharge threshold, either by a load on the battery or due to battery removal, the bqTINY begins a battery absent detection test. This test involves enabling a detection current, $I_{(DETECT)}$, for a period of $t_{(DETECT)}$ and checking to see if the battery voltage is below the pre-charge threshold, $V_{(LOWV)}$. Following this, the precharge current, $I_{O(PRECHG)}$ is applied for a period of $t_{(DETECT)}$ and the battery voltage checked again to be above the recharge threshold. The purpose is to attempt to close a battery pack with an open protector, if one is connected to the bqTINY. Passing both of the discharge and charging tests indicates a battery absent fault at the STAT pins. Failure of either test starts a new charge cycle. For the absent battery condition the voltage on the BAT pin rises and falls between the $V_{(LOWV)}$ and $V_{O(REG)}$ thresholds indefinitely. See Figure 7.
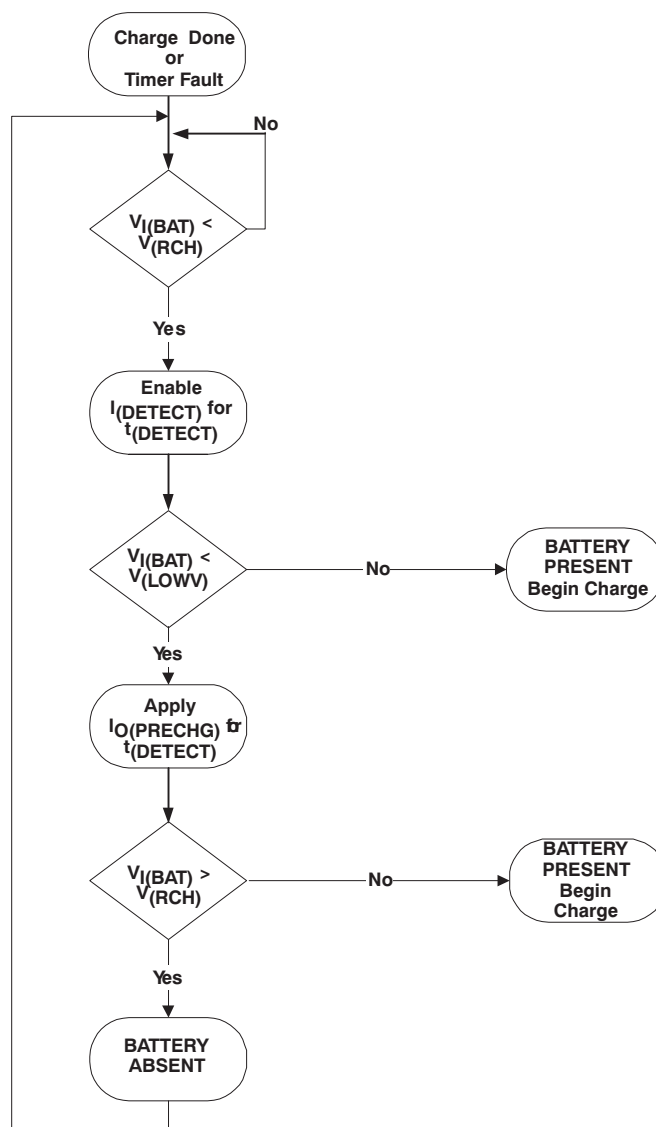

Figure 7. Battery Absent Detection

Product Folder Link(s): *bq24010, bq24012 bq24013, bq24014, bq24018*

TIMER FAULT RECOVERY

As shown in Figure 5, bqTINY provides a recovery method to deal with timer fault conditions. The following conditions summarize this method.

Condition #1: Charge voltage above recharge threshold ($V_{(RCH)}$) and timeout fault occurs

Recovery method: bqTINY waits for the battery voltage to fall below the recharge threshold. This could happen as a result of a load on the battery, self-discharge or battery removal. Once the battery falls below the recharge threshold, the bqTINY clears the fault and enters the battery absent detection routine. A POR or CE toggle also clears the fault.

Condition #2: Charge voltage below recharge threshold ($V_{(RCH)}$) and timeout fault occurs.

Recovery method: Under this scenario, the bqTINY applies the $I_{(FAULT)}$ current. This small current is used to detect a battery removal condition and remains on as long as the battery voltage stays below the recharge threshold. If the battery voltage goes above the recharge threshold, then the bqTINY disables the $I_{(FAULT)}$ current and executes the recovery method described for condition #1. Once the battery falls below the recharge threshold, the bqTINY clears the fault and enters the battery absent detection routine. A POR or CE toggle also clears the fault.

bq24010, bq24012
bq24013, bq24014, bq24018

SLUS530J−SEPTEMBER 2002−REVISED DECEMBER 2008

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APPLICATION INFORMATION

SELECTING INPUT CAPACITOR

In most applications, all that is needed is a high-frequency decoupling capacitor. A 0.47-µF ceramic, placed in close proximity to V_{CC} and V_{SS} pins, works well. The bqTINY is designed to work with both regulated and unregulated external dc supplies. If a non-regulated supply is chosen, the supply unit should have enough capacitance to hold up the supply voltage to the minimum required input voltage at maximum load. If not, more capacitance has to be added to the input of the charger.

SELECTING OUTPUT CAPACITOR

The bqTINY requires only a small output capacitor for loop stability. A 0.1-µF ceramic capacitor placed between the BAT and ISET pins is typically sufficient for embedded applications (i.e., non-removable battery packs). For application with removable battery packs a 1-µF ceramic capacitor ensure proper operation of the battery detection circuitry. Note that the output capacitor can also be placed between BAT and VSS pins.

THERMAL CONSIDERATIONS

The bqTINY is packaged in a thermally enhanced MLP (also referred to as QFN) package. The package includes a thermal pad to provide an effective thermal contact between the device and the printed circuit board (PCB). Full PCB design guidelines for this package are provided in the application note entitled, *QFN/SON PCB Attachment* application note (SLUA271).

The most common measure of package thermal performance is thermal impedance (θ_{JA}) measured (or modeled) from the device junction to the air surrounding the package surface (ambient). The mathematical expression for θ_{JA} is:

$$\theta_{JA} = \frac{T_J \times T_A}{P}$$

(7)

Where:

T_J = device junction temperature

T_A = ambient temperature

P = device power dissipation

Factors that can greatly influence the measurement and calculation of θ_{JA} include:

- whether or not the device is board mounted
- trace size, composition, thickness, and geometry
- orientation of the device (horizontal or vertical)
- volume of the ambient air surrounding the device under test and airflown
- whether other surfaces are in close proximity to the device being tested

The device power dissipation, P, is a function of the charge rate and the voltage drop across the internal PowerFET. It can be calculated from the following equation:

$$P = V_{IN} - V_{I(BAT)} \times I_{O(OUT)}$$

(8)

Due to the charge profile of Li-xx batteries, the maximum power dissipation is typically seen at the beginning of the charge cycle when the battery voltage is at its lowest. See Figure 2.

PCB LAYOUT CONSIDERATIONS

It is important to pay special attention to the PCB layout. The following provides some guidelines:

- To obtain optimal performance, the decoupling capacitor from V_{CC} to V_{SS} and the output filter capacitors from BAT to ISET should be placed as close as possible to the bqTINY, with short trace runs to both signal and V_{SS} pins.
- All low-current V_{SS} connections should be kept separate from the high-current charge or discharge paths from the battery. Use a single-point ground technique incorporating both the small signal ground path and the power ground path.
- The BAT pin is the voltage feedback to the device and should be connected with its trace as close to the battery pack as possible.
- The high current charge paths into IN and from the OUT pins must be sized appropriately for the maximum charge current in order to avoid voltage drops in these traces.
- The bqTINY is packaged in a thermally enhanced MLP package. The package includes a thermal pad to provide an effective thermal contact between the device and the printed circuit board (PCB). Full PCB design guidelines for this package are provided in the application note entitled: *QFN/SON PCB Attachment Application Note* (SLUA271).
- There is an internal electrical connection between the exposed thermal pad and V_{SS} pin of the device. The exposed thermal pad must be connected to the same potential as the VSS pin on the printed circuit board. Do not use the thermal pad as the primary ground input for the device. V_{SS} pin must be connected to ground at all times.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)
BQ24010DRCR	ACTIVE	SON	DRC	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24010DRCRG4	ACTIVE	SON	DRC	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24012DRCR	ACTIVE	SON	DRC	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24012DRCRG4	ACTIVE	SON	DRC	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24013DRCR	ACTIVE	SON	DRC	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24013DRCRG4	ACTIVE	SON	DRC	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24014DRCR	ACTIVE	SON	DRC	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24014DRCRG4	ACTIVE	SON	DRC	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24018DRCR	ACTIVE	SON	DRC	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24018DRCRG4	ACTIVE	SON	DRC	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24018DRCT	ACTIVE	SON	DRC	10	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
BQ24018DRCTG4	ACTIVE	SON	DRC	10	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check
http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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PACKAGE MATERIALS INFORMATION

TAPE AND REEL INFORMATION

REEL DIMENSIONS

TAPE DIMENSIONS

A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
BQ24010DRCR	SON	DRC	10	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
BQ24012DRCR	SON	DRC	10	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
BQ24013DRCR	SON	DRC	10	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
BQ24014DRCR	SON	DRC	10	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
BQ24018DRCR	SON	DRC	10	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
BQ24018DRCT	SON	DRC	10	250	180.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2

TAPE AND REEL BOX DIMENSIONS

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
BQ24010DRCR	SON	DRC	10	3000	367.0	367.0	35.0
BQ24012DRCR	SON	DRC	10	3000	367.0	367.0	35.0
BQ24013DRCR	SON	DRC	10	3000	367.0	367.0	35.0
BQ24014DRCR	SON	DRC	10	3000	367.0	367.0	35.0
BQ24018DRCR	SON	DRC	10	3000	367.0	367.0	35.0
BQ24018DRCT	SON	DRC	10	250	210.0	185.0	35.0

DRC (S−PVSON−N10)   PLASTIC SMALL OUTLINE NO−LEAD

$\frac{3,10}{2,90}$ [A]

[B]

$\frac{3,10}{2,90}$

PIN 1 INDEX AREA
TOP AND BOTTOM

$\frac{1,00}{0,80}$

0,20 REF.

[△|0,08]   SEATING PLANE

[C]

$\frac{0,05}{0,00}$

10X $\frac{0,50}{0,30}$

[0,50]

1   5

THERMAL PAD

SIZE AND SHAPE
SHOWN ON SEPARATE SHEET

10   6

10X $\frac{0,30}{0,18}$

⊕	0,10 Ⓜ	C	A	B
	0,05 Ⓜ	C		
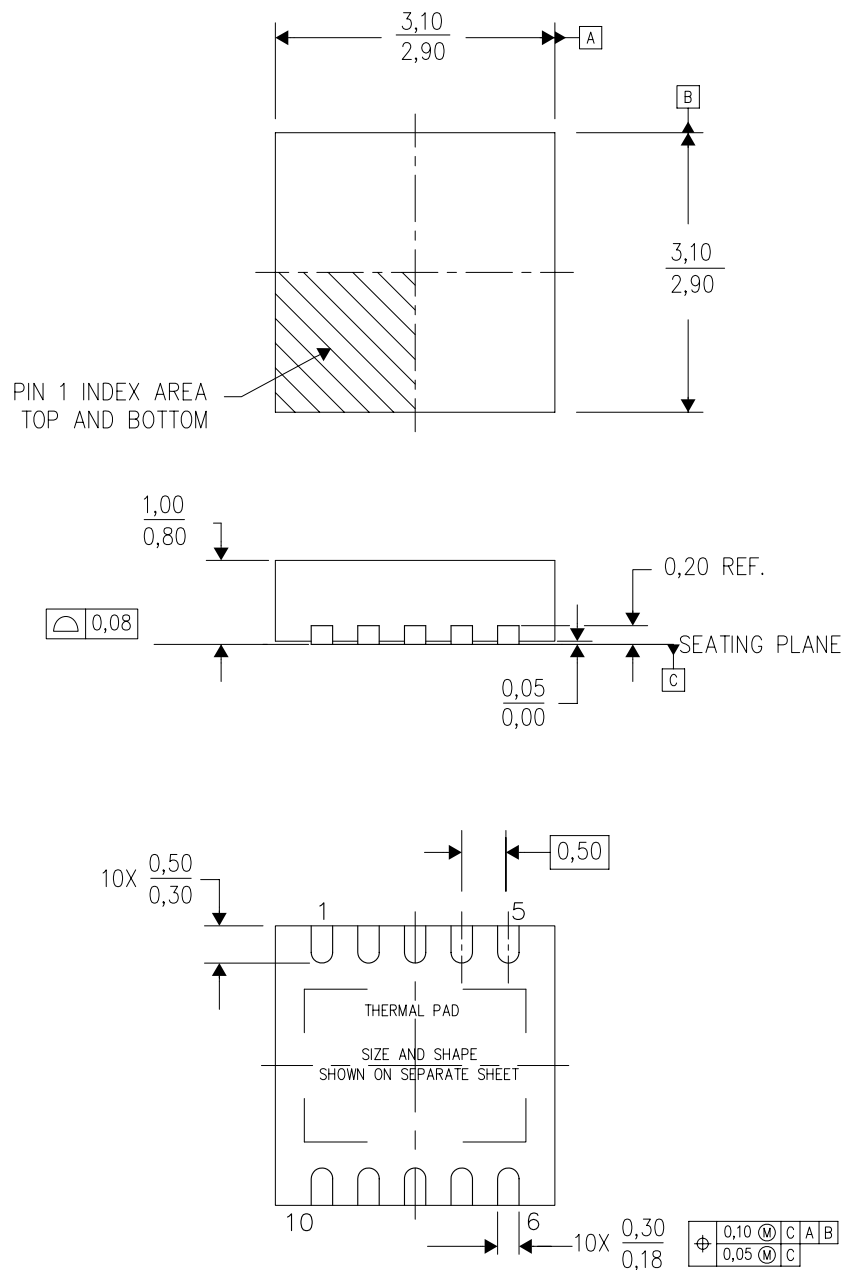
4204102−3/L 09/11

NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M−1994.
       B. This drawing is subject to change without notice.
       C. Small Outline No−Lead (SON) package configuration.
       D. The package thermal pad must be soldered to the board for thermal and mechanical performance, if present.
       E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features
           and dimensions, if present
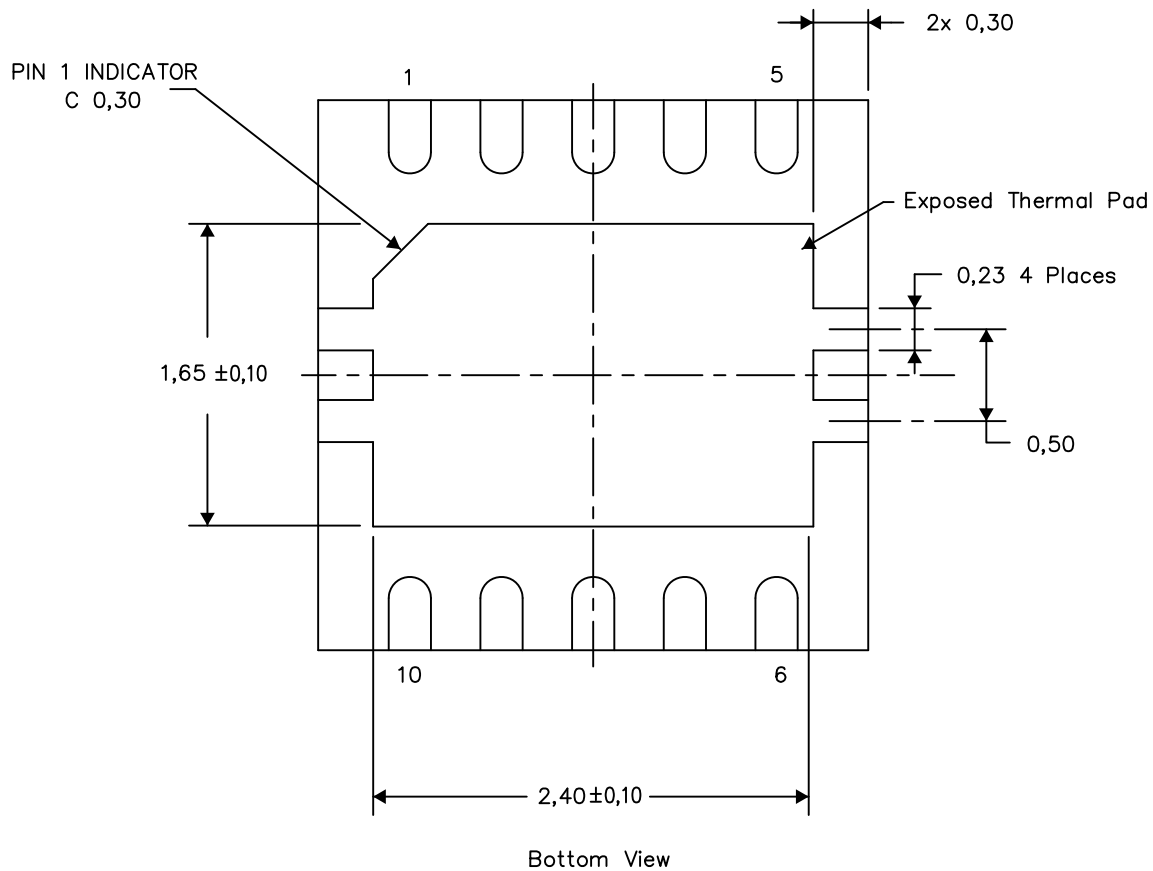
DRC (S−PVSON−N10)   PLASTIC SMALL OUTLINE NO−LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No−Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.
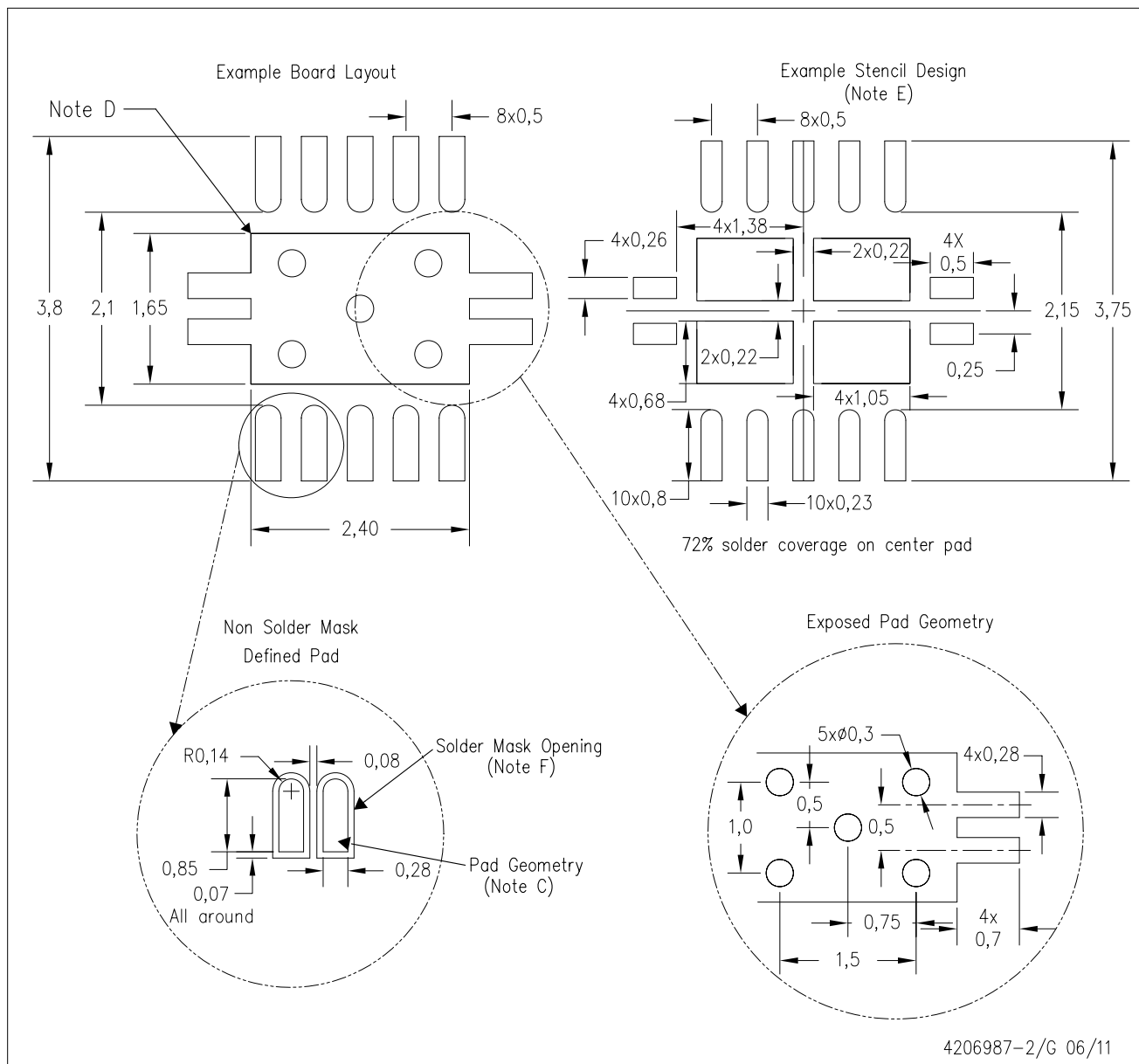

Bottom View

Exposed Thermal Pad Dimensions

4206565−3/N 07/12

NOTE: A.   All linear dimensions are in millimeters

DRC (S−PVSON−N10)   PLASTIC SMALL OUTLINE NO−LEAD

Example Board Layout

Note D

8x0,5

3,8 2,1 1,65

2,40

Example Stencil Design
(Note E)

8x0,5

4x0,26   4x1,38
                    2x0,22   4X
                              0,5
                                        2,15 3,75
2x0,22
4x0,68   4x1,05   0,25

10x0,8   10x0,23

72% solder coverage on center pad

Non Solder Mask
Defined Pad

R0,14   0,08   Solder Mask Opening
                         (Note F)
0,85
0,07   0,28   Pad Geometry
All around   (Note C)

Exposed Pad Geometry

5xØ0,3   4x0,28
        0,5
1,0   0,5
        0,75   4x
1,5   0,7

4206987−2/G 06/11

NOTES: A. All linear dimensions are in millimeters.
        B. This drawing is subject to change without notice.
        C. Publication IPC−7351 is recommended for alternate designs.
        D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat−Pack
            Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets
            for specific thermal information, via requirements, and recommended board layout. These documents are available at
            www.ti.com <http://www.ti.com>.
        E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should
            contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
        F. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.

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